

## S4040xQx Series

RoHS



### Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
$V_{DRM}/V_{RRM}$	400	V
$I_{GT}$	15 to 65	mA

### Description

The S4040xQx series of SCRs offer fast turn-off time ( $t_q$ ) characteristics required for applications such as power inverters, switching regulator, and high frequency pulse circuits.

These fast turn-off time SCRs offer high  $dv/dt$  and high  $di/dt$  characteristics required in higher frequency (>1000 PPS) switching circuits.

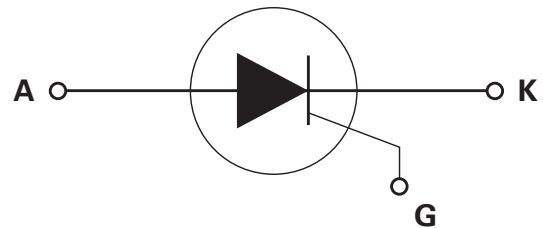
### Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 400 V
- Surge capability up to 520 A
- TO-220 and TO-263 packages

### Applications

Fast turn-off time SCRs are ideal for multi phase voltage regulator circuits, DC/AC inverters, and higher frequency pulsing power supplies.

### Schematic Symbol



### Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$I_{T(RMS)}$	RMS on-state current	$T_c = 100^\circ\text{C}$	40	A
$I_{T(AV)}$	Average on-state current	$T_c = 100^\circ\text{C}$	25.0	A
$I_{TSM}$	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$ ; $T_j$ (initial) = $25^\circ\text{C}$	430	A
		single half cycle; $f = 60\text{Hz}$ ; $T_j$ (initial) = $25^\circ\text{C}$	520	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3\text{ ms}$	1122	$\text{A}^2\text{s}$
$di/dt$	Critical rate of rise of on-state current	$f = 60\text{Hz}$ ; $T_j = 125^\circ\text{C}$	175	$\text{A}/\mu\text{s}$
$I_{GM}$	Peak gate current	$T_j = 125^\circ\text{C}$	3.5	A
$P_{G(AV)}$	Average gate power dissipation	$T_j = 125^\circ\text{C}$	0.8	W
$T_{stg}$	Storage temperature range		-40 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		-40 to 125	$^\circ\text{C}$

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)**

Symbol	Test Conditions		Sxx40xQ	Sxx40xQ2	Sxx40xQ3	Unit
$I_{GT}$	$V_D = 12\text{V}; R_L = 30\ \Omega$	MAX.	35	45	65	mA
		MIN.	15	30	38	
$V_{GT}$		MAX.	1.5			V
$I_{GT}$	$V_D = 12\text{V}; R_L = 30\ \Omega; T_J = -40^\circ\text{C}$	MAX.	75	95	160	mA
dv/dt	$V_D = V_{DRM};$ gate open; $T_J = 100^\circ\text{C}$	MIN.	650			V/ $\mu\text{s}$
	$V_D = V_{DRM};$ gate open; $T_J = 125^\circ\text{C}$		550			
$V_{GD}$	$V_D = V_{DRM}; R_L = 3.3\ \text{k}\Omega; T_J = 125^\circ\text{C}$	MIN.	0.2			V
$I_H$	$I_T = 400\text{mA}$ (initial)	MAX.	70	120	200	mA
$t_q$	(1)	MAX.	15	12	5	$\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}; PW = 15\ \mu\text{s}; I_T = 80\text{A}$	TYP.	3.0		3.5	$\mu\text{s}$

Note :

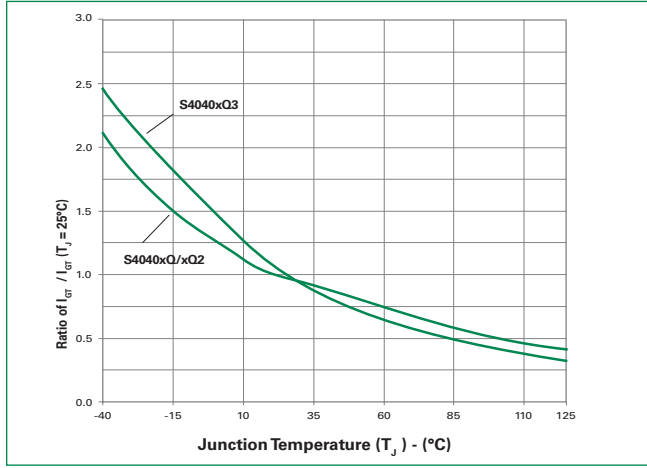
 (1)  $I_T=0.5\text{A}; t_p=50\ \mu\text{s}; dv/dt=5\text{V}/\mu\text{s}; di/dt=30\text{A}/\mu\text{s}$ 
**Static Characteristics**

Symbol	Test Conditions		S4040xQ	S4040xQ2	S4040xQ3	Unit
$V_{TM}$	$I_T = 80\text{A}; t_p = 380\ \mu\text{s}$	MAX.	1.8		2.2	V
$I_{DRM} / I_{RRM}$	$V_{DRM} / V_{RRM}$	$T_J = 25^\circ\text{C}$	10			$\mu\text{A}$
		$T_J = 100^\circ\text{C}$	1000			
		$T_J = 125^\circ\text{C}$	2000			

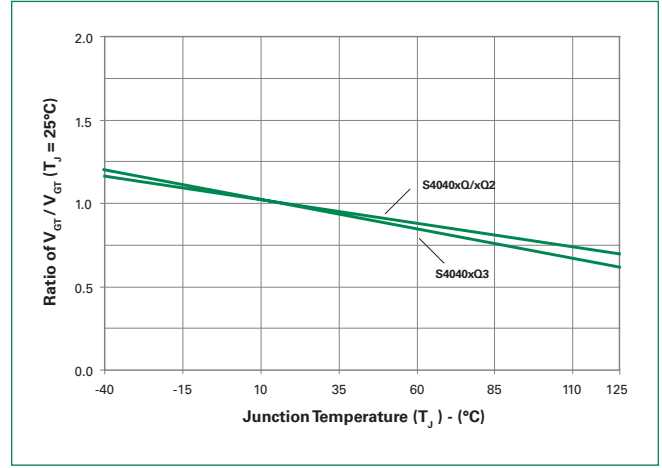
**Thermal Resistances**

Symbol	Parameter	Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	0.6	$^\circ\text{C}/\text{W}$
$R_{\theta(J-A)}$	Junction to ambient	40	$^\circ\text{C}/\text{W}$

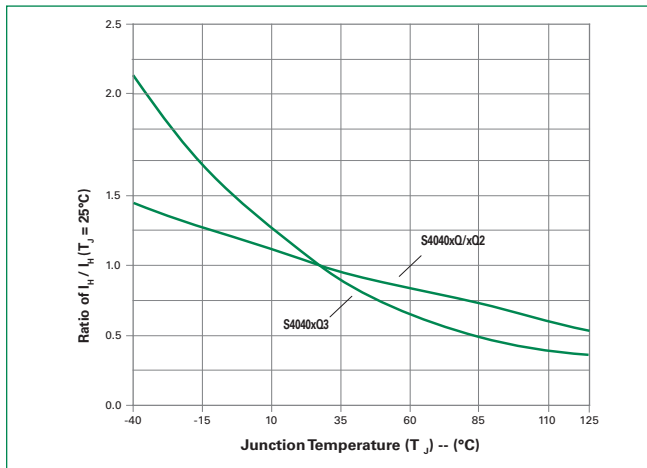
**Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature**



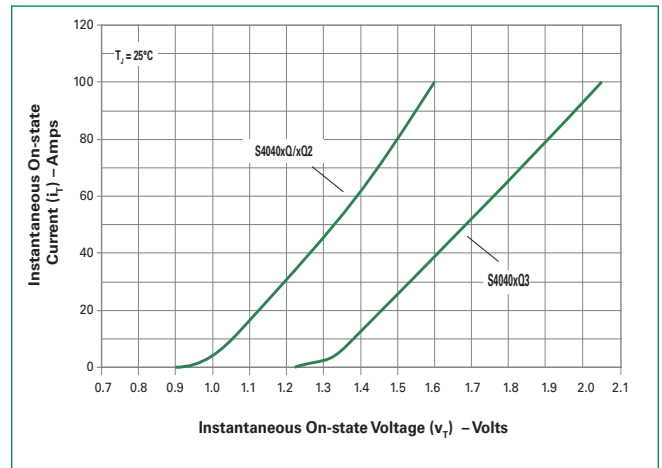
**Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature**



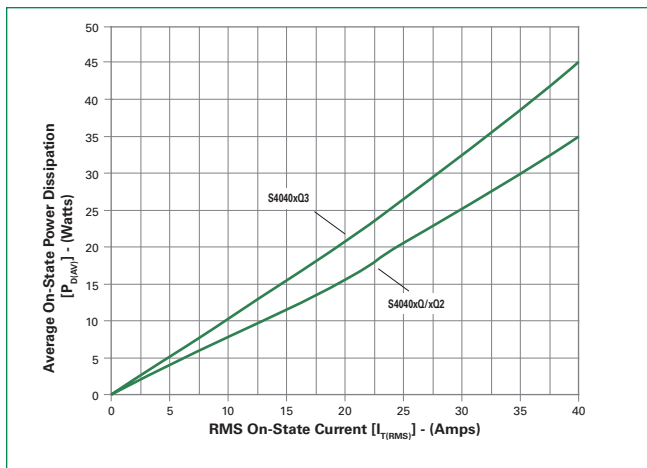
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



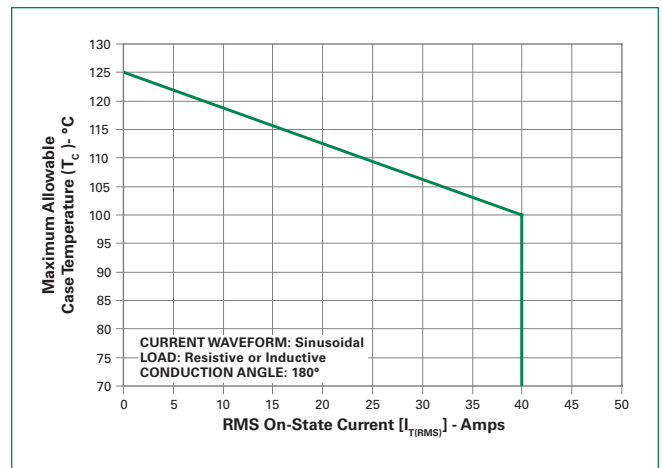
**Figure 4: On-State Current vs. On-State Voltage (Typical)**



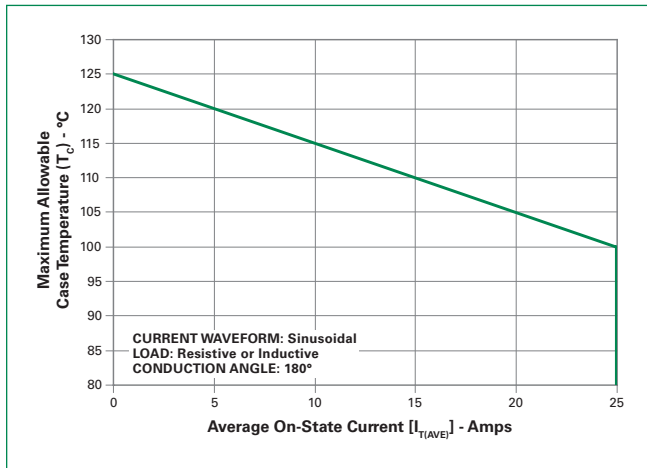
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



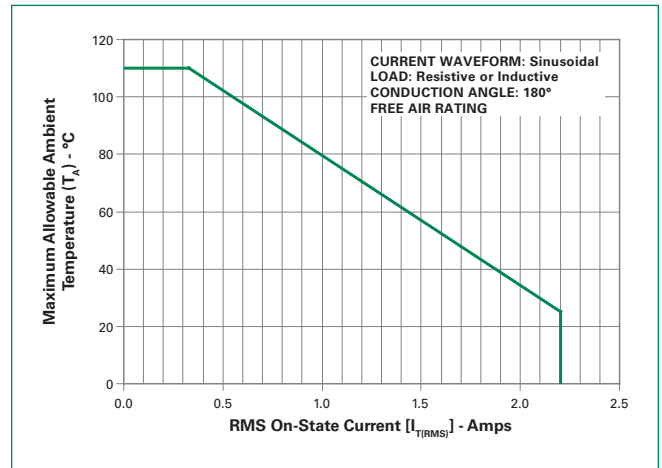
**Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current**



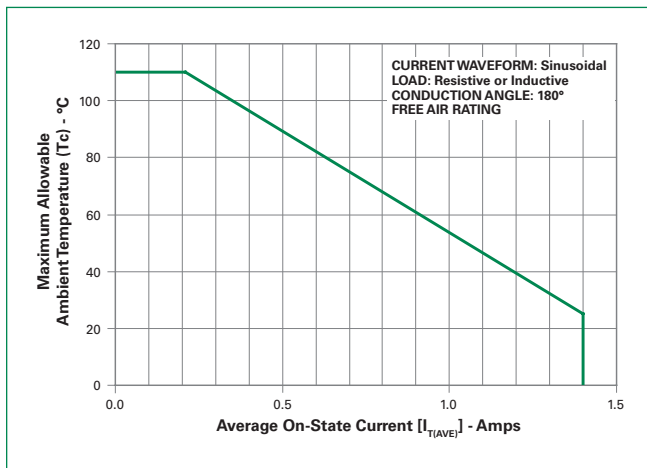
**Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current**



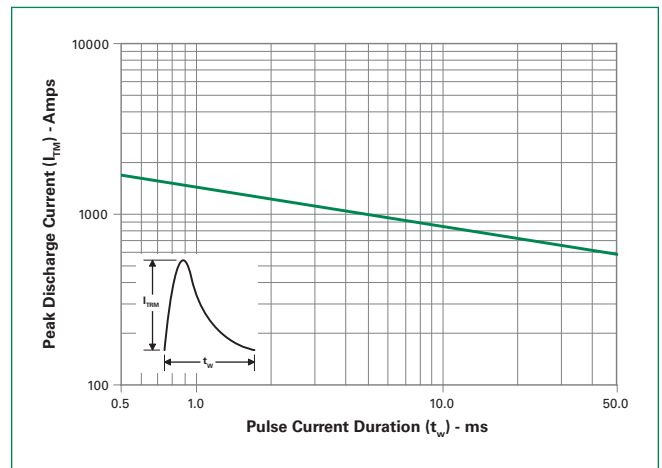
**Figure 8: Maximum Allowable Ambient Temperature vs. RMS On-State Current**



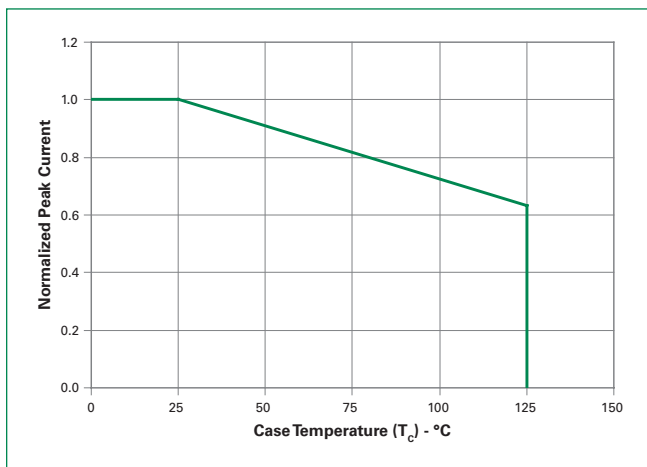
**Figure 9: Maximum Allowable Ambient Temperature vs. Average On-State Current**



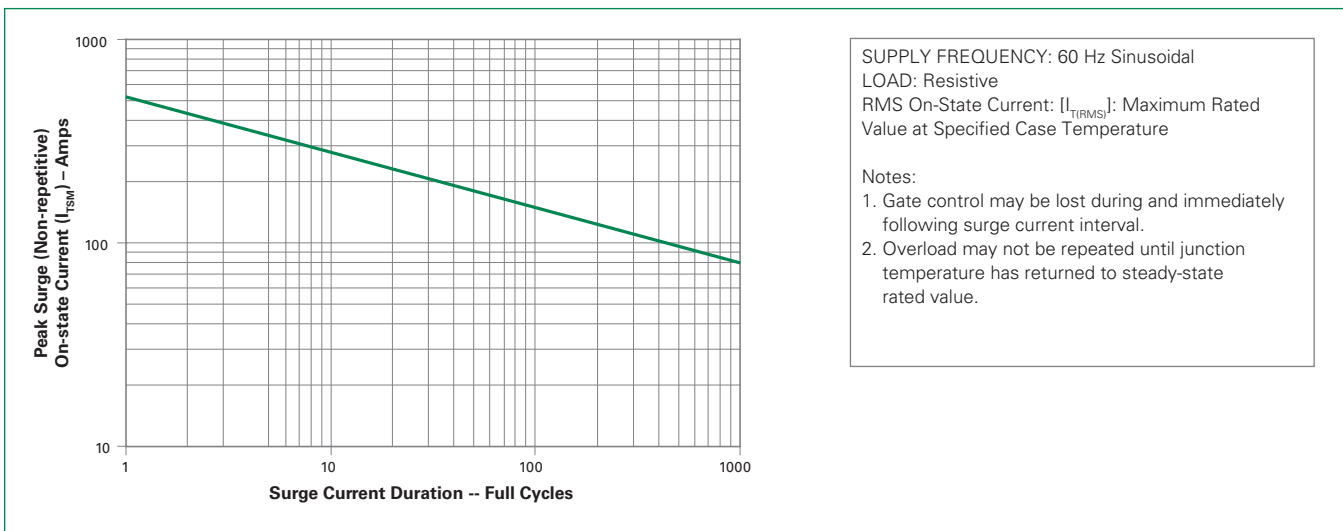
**Figure 10: Peak Capacitor Discharge Current**



**Figure 11: Peak Capacitor Discharge Current Derating**

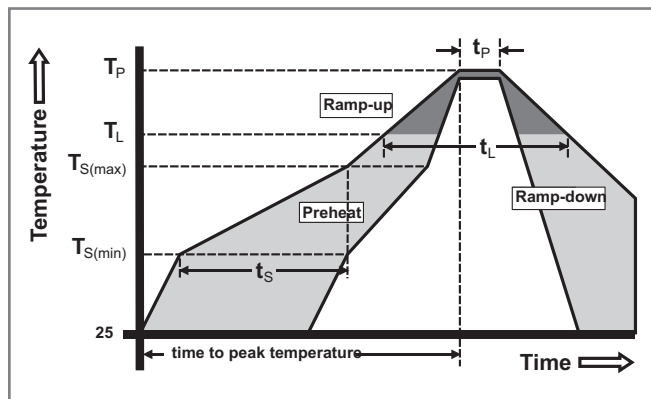


**Figure 12: Surge Peak On-State Current vs. Number of Cycles**



**Soldering Parameters**

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



**Physical Specifications**

<b>Terminal Finish</b>	100% Matte Tin-plated
<b>Body Material</b>	UL recognized epoxy meeting flammability classification 94V-0
<b>Lead Material</b>	Copper Alloy

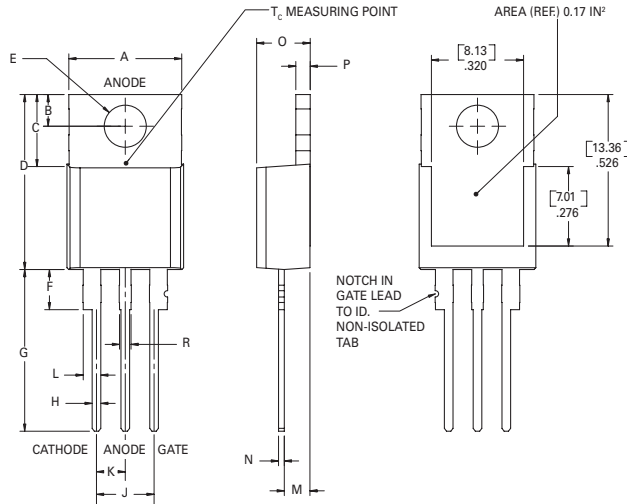
**Design Considerations**

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

**Environmental Specifications**

Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

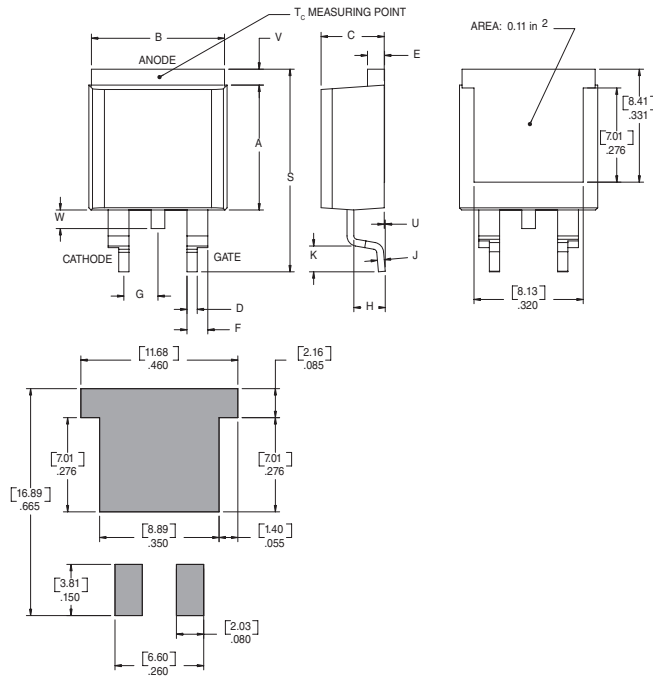
**Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead**



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

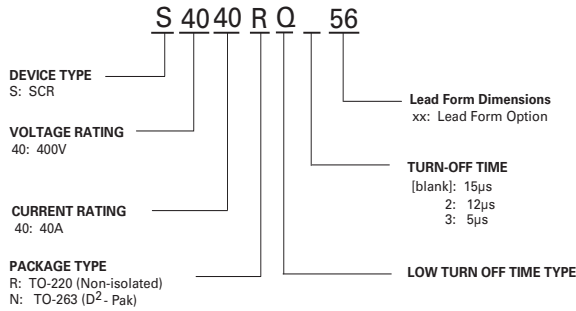
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

**Dimensions – TO- 263 (N-package) – D<sup>2</sup>-Pak Surface Mount**



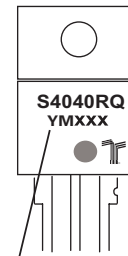
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.63	0.89
E	0.048	0.055	1.22	1.40
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.083	0.093	2.11	2.36
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.87
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

**Part Numbering System**



**Part Marking System**

TO-220 AB - (R Package)  
TO-263 (N Package)



Date Code Marking  
Y: Year Code  
M: Month Code  
XXX: Lot Trace Code